

## GANKIBAN Type: CN10MM

### GaN Wafers

GaN wafers enable "GaN-on-GaN" structure of GaN-based optoelectronic and electronic devices such as blue/green laser diodes, light emitting diodes, high-power switching transistors, and RF transistors. GANKIBAN CN10MM is an n<sup>+</sup> wafer produced by SixPoint's proprietary NEAT (near equilibrium ammonothermal) method. High carrier concentration attains low series resistance for reduction of heat generation during high-current operation, It is suitable for vertical devices including edge-emitting laser diodes, vertical high-power pn diodes and vertical high-power transistors.

### Applications

R&D of GaN-based devices using homoepitaxy

### Specifications

Wafer size	10 x 10 mm, with m-plane flat, usable area > 90%
Wafer thickness	300 ~ 400 micron
Orientation	C plane Miscut angle 0°±0.2° toward A, 0.4°±0.2° toward M
Surface finish	Ga-face --- CMP N-face --- as processed
XRD FWHM from (002)	< 200 arcsec (typical value is 100 arcsec)
Conduction type	n <sup>+</sup> -type (n > 1x10 <sup>19</sup> cm <sup>-3</sup> )

